

# Field Stop Trench IGBT

## 650 V, 40 A

### FGHL40T65MQD

Field stop 4th generation mid speed IGBT technology and full current rated copak Diode technology.

#### Features

- Maximum Junction Temperature:  $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 1.45\text{ V (Typ.) @ } I_C = 40\text{ A}$
- 100% of the Parts are Tested for  $I_{LM}$  (Note 2)
- Smooth & Optimized Switching
- Tight Parameter Distribution
- RoHS Compliant

#### Typical Applications

- Solar Inverter
- UPS, ESS
- PFC, Converters

#### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Collector-to-Emitter Voltage	$V_{CES}$	650	V	
Gate-to-Emitter Voltage	$V_{GES}$	$\pm 20$	V	
Transient Gate-to-Emitter Voltage	$V_{GES}$	$\pm 30$	V	
Collector Current (Note 1)	$I_C$	$T_C = 25^\circ\text{C}$	80	A
		$T_C = 100^\circ\text{C}$	40	
Pulsed Collector Current (Note 2)	$I_{LM}$	160	A	
Pulsed Collector Current (Note 3)	$I_{CM}$	160	A	
Diode Forward Current (Note 1)	$I_F$	$T_C = 25^\circ\text{C}$	40	A
		$T_C = 65^\circ\text{C}$	25	
Pulsed Diode Maximum Forward Current	$I_{FM}$	160	A	
Non-Repetitive Forward Surge Current (Half-Sine Pulse, $t_p = 8.3\text{ ms}$ , $T_C = 25^\circ\text{C}$ ) (Half-Sine Pulse, $t_p = 8.3\text{ ms}$ , $T_C = 150^\circ\text{C}$ )	$I_{F,SM}$		85	A
			80	
Maximum Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	238	W
		$T_C = 100^\circ\text{C}$	119	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Maximum Lead Temperature for Soldering Purposes (1/8" from case for 5 s)	$T_L$	300	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

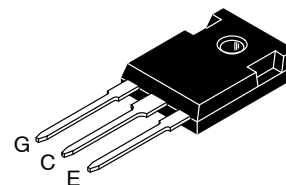
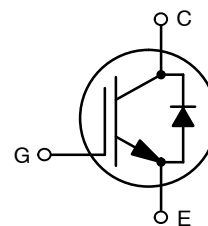
1. Value limit by bond wire
2.  $V_{CC} = 400\text{ V}$ ,  $V_{GE} = 15\text{ V}$ ,  $I_C = 160\text{ A}$ ,  $R_G = 14\ \Omega$ , Inductive Load, 100% Tested
3. Repetitive rating: Pulse width limited by max. junction temperature



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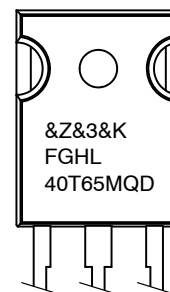
[www.onsemi.com](http://www.onsemi.com)

$BV_{CES}$	$V_{CE(sat)}$ TYP	$I_C$ MAX
650 V	1.45 V	40 A



TO-247 LONG LEADS  
CASE 340CX

#### MARKING DIAGRAM



&Z = Assembly Plant Code  
 &3 = 3-Digit Date Code  
 &K = 2-Digit Lot Traceability Code  
 FGHL40T65MQD = Specific Device Code

#### ORDERING INFORMATION

Device	Package	Shipping
FGHL40T65MQD	TO-247-3L	30 Units / Rail

# FGHL40T65MQD

**Table 1. THERMAL CHARACTERISTICS**

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-to-Case, for IGBT	$R_{\theta JC}$	0.63	°C/W
Thermal Resistance Junction-to-Case, for Diode	$R_{\theta JC}$	1.6	
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	40	

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTIC</b>						
Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$BV_{CES}$	650	-	-	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$\Delta BV_{CES} / \Delta T_J$	-	0.6	-	V/°C
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$	$I_{CES}$	-	-	250	μA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	-	-	±400	nA
<b>ON CHARACTERISTIC</b>						
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 40\text{ mA}$	$V_{GE(th)}$	3.0	4.5	6.0	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^\circ\text{C}$	$V_{CE(sat)}$	-	1.45 1.77	1.8 -	V
<b>DYNAMIC CHARACTERISTIC</b>						
Input capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$	-	2756	-	pF
Output capacitance		$C_{oes}$	-	64	-	
Reverse transfer capacitance		$C_{res}$	-	9	-	
Gate charge total	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	$Q_g$	-	86	-	nC
Gate-to-Emitter charge		$Q_{ge}$	-	16	-	
Gate-to-Collector charge		$Q_{gc}$	-	21	-	
<b>SWITCHING CHARACTERISTIC, INDUCTIVE LOAD</b>						
Turn-on delay time	$T_C = 25^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 20\text{ A}$ $R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	-	20	-	ns
Rise time		$t_r$	-	13	-	
Turn-off delay time		$t_{d(off)}$	-	116	-	
Fall time		$t_f$	-	51	-	
Turn-on switching loss		$E_{on}$	-	0.33	-	mJ
Turn-off switching loss		$E_{off}$	-	0.26	-	
Total switching loss		$E_{ts}$	-	0.59	-	
Turn-on delay time	$T_C = 25^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 40\text{ A}$ $R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	-	22	-	ns
Rise time		$t_r$	-	30	-	
Turn-off delay time		$t_{d(off)}$	-	109	-	
Fall time		$t_f$	-	46	-	
Turn-on switching loss		$E_{on}$	-	0.86	-	mJ
Turn-off switching loss		$E_{off}$	-	0.52	-	
Total switching loss		$E_{ts}$	-	1.38	-	

# FGHL40T65MQD

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified) (continued)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>SWITCHING CHARACTERISTIC, INDUCTIVE LOAD</b>						
Turn-on delay time	$T_C = 175^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 20\text{ A}$ $R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	–	20	–	ns
Rise time		$t_r$	–	14	–	
Turn-off delay time		$t_{d(off)}$	–	127	–	
Fall time		$t_f$	–	76	–	
Turn-on switching loss		$E_{on}$	–	0.60	–	mJ
Turn-off switching loss		$E_{off}$	–	0.42	–	
Total switching loss		$E_{ts}$	–	1.02	–	
Turn-on delay time	$T_C = 175^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 40\text{ A}$ $R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}$ Inductive Load	$t_{d(on)}$	–	20	–	ns
Rise time		$t_r$	–	32	–	
Turn-off delay time		$t_{d(off)}$	–	119	–	
Fall time		$t_f$	–	63	–	
Turn-on switching loss		$E_{on}$	–	1.28	–	mJ
Turn-off switching loss		$E_{off}$	–	0.77	–	
Total switching loss		$E_{ts}$	–	2.05	–	
<b>DIODE CHARACTERISTIC2.5</b>						
Diode Forward Voltage	$I_F = 40\text{ A}, T_C = 25^\circ\text{C}$ $I_F = 40\text{ A}, T_C = 175^\circ\text{C}$	$V_{FM}$	–	2.55 2.3	2.85 –	V
Reverse Recovery Energy	$I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, T_C = 175^\circ\text{C}$	$E_{rec}$	–	56	–	$\mu\text{J}$
Diode Reverse Recovery Time	$I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, T_C = 25^\circ\text{C}$ $I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, T_C = 175^\circ\text{C}$	$T_{rr}$	–	33 222	–	ns
Diode Reverse Recovery Charge	$I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, T_C = 25^\circ\text{C}$ $I_F = 40\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, T_C = 175^\circ\text{C}$	$Q_{rr}$	–	47 759	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# FGHL40T65MQD

## TYPICAL CHARACTERISTICS

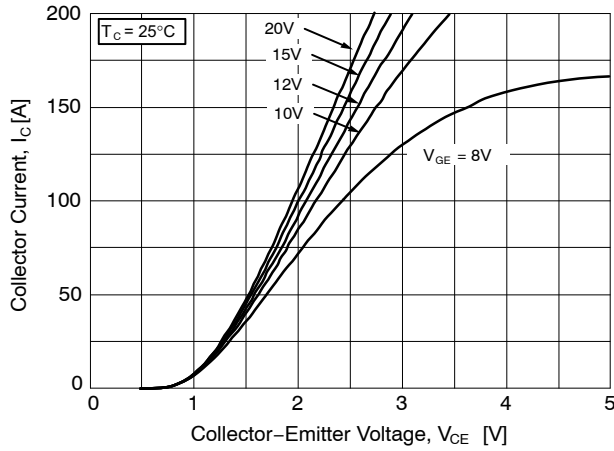


Figure 1. Typical Output Characteristics  
( $T_J = 25^\circ\text{C}$ )

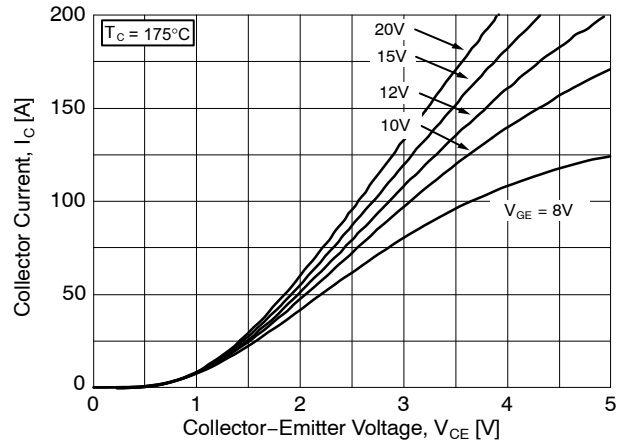


Figure 2. Typical Output Characteristics  
( $T_J = 175^\circ\text{C}$ )

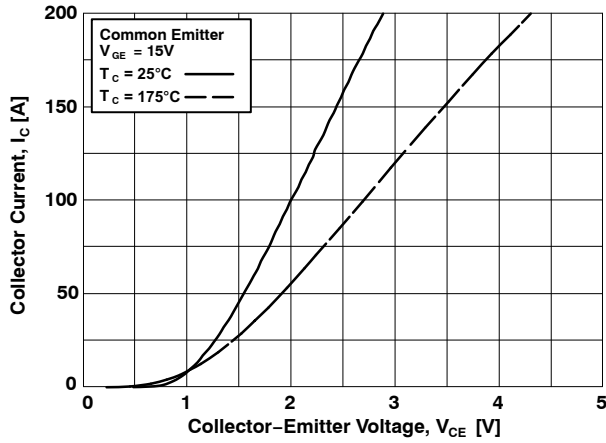


Figure 3. Typical Saturation Voltage Characteristics

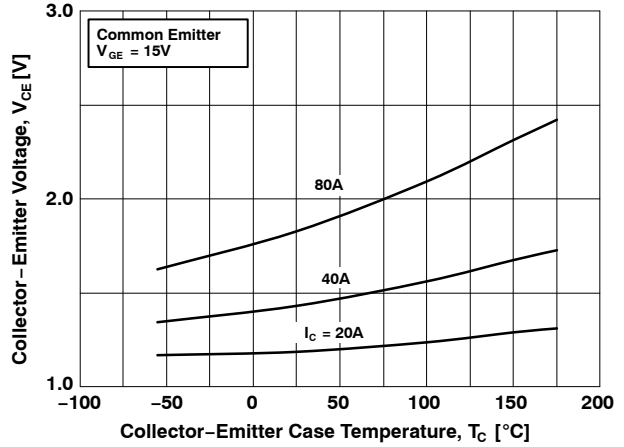


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

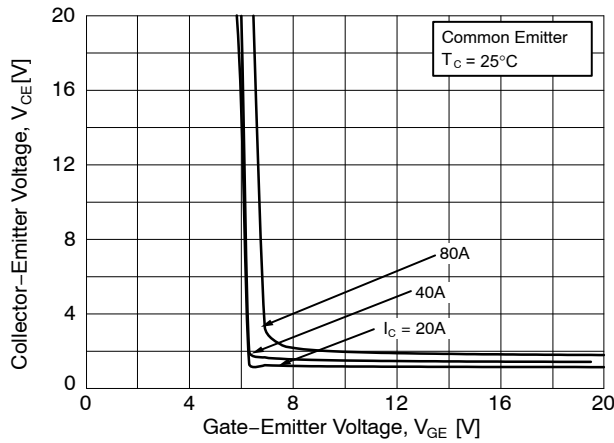


Figure 5. Saturation Voltage vs.  $V_{GE}$  ( $T_J = 25^\circ\text{C}$ )

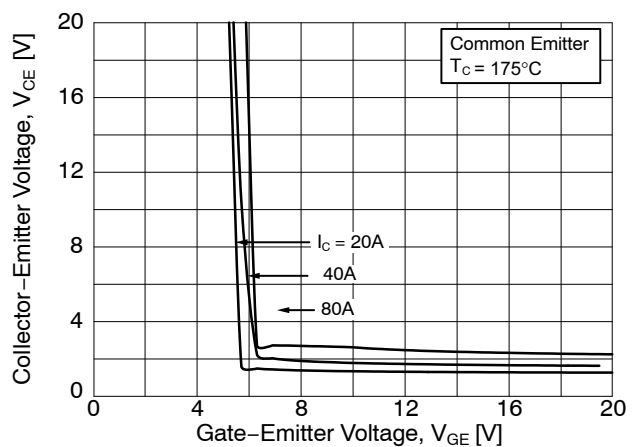


Figure 6. Saturation Voltage vs.  $V_{GE}$  ( $T_J = 175^\circ\text{C}$ )

# FGHL40T65MQD

## TYPICAL CHARACTERISTICS (continued)

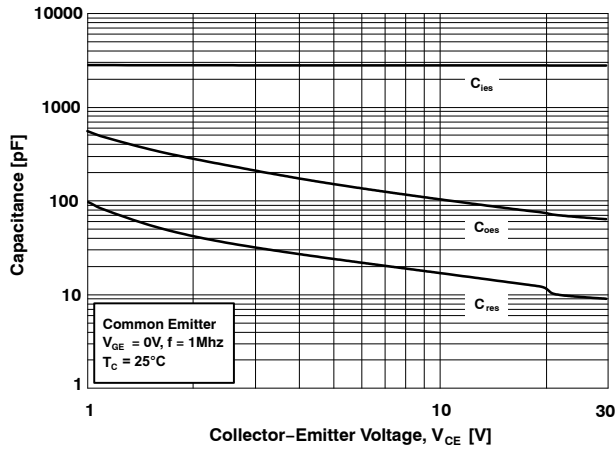


Figure 7. Capacitance Characteristics

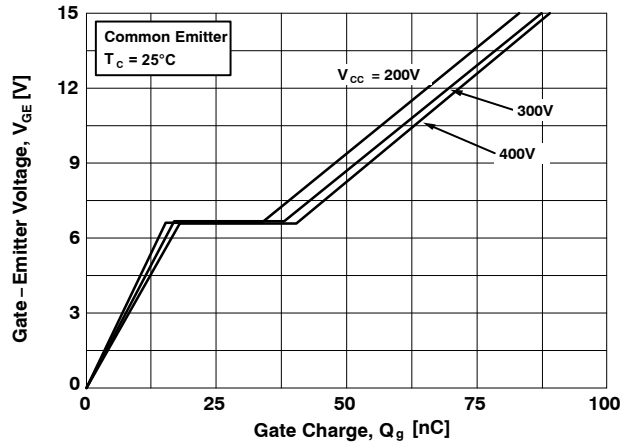


Figure 8. Gate Charge Characteristics

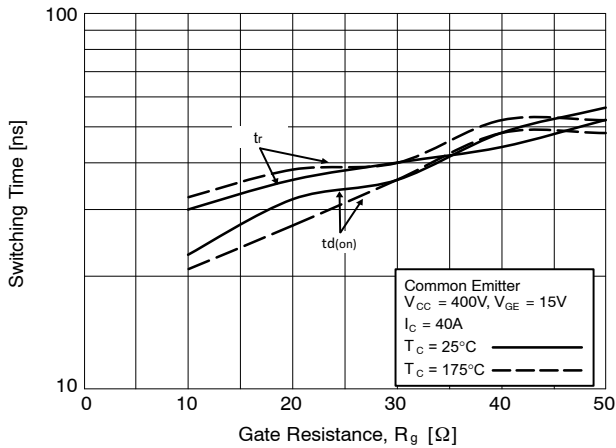


Figure 9. Turn-On Characteristics vs. Gate Resistance

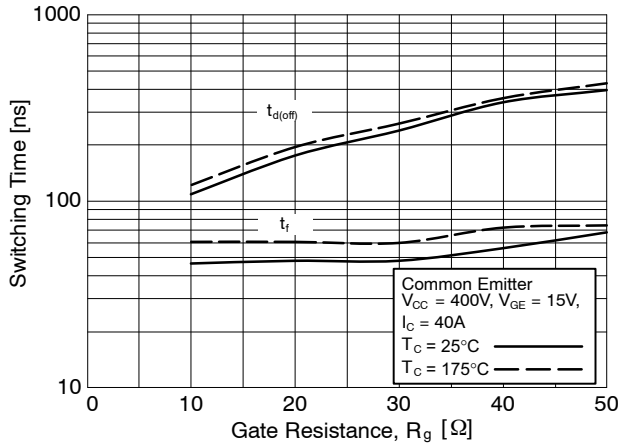


Figure 10. Turn-Off Characteristics vs. Gate Resistance

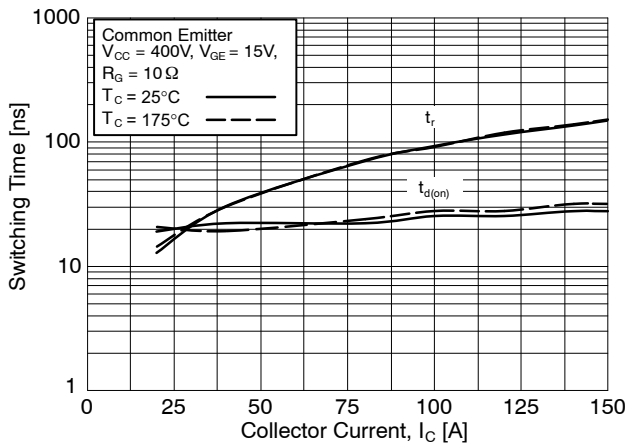


Figure 11. Turn-On Characteristics vs. Collector Current

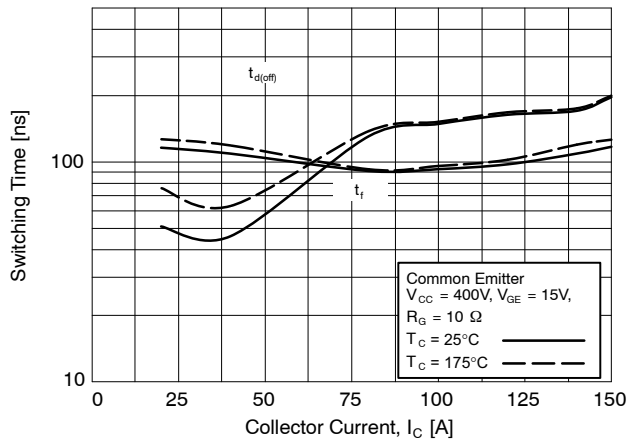


Figure 12. Turn-Off Characteristics vs. Collector Current

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## TYPICAL CHARACTERISTICS (continued)

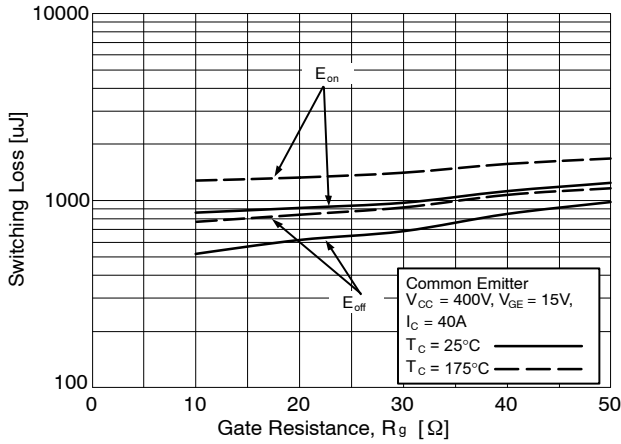


Figure 13. Switching Loss vs. Gate Resistance

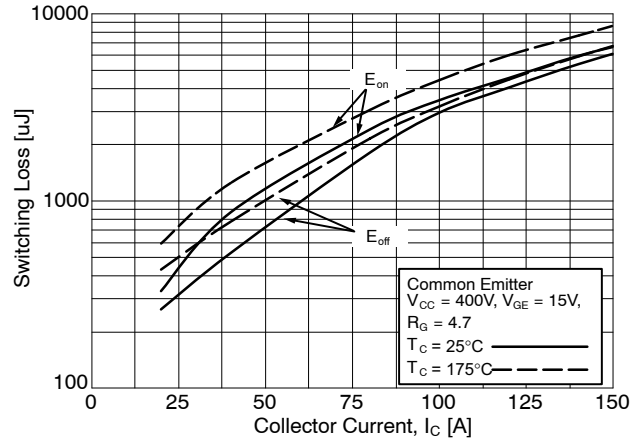


Figure 14. Switching Loss vs. Collector Current

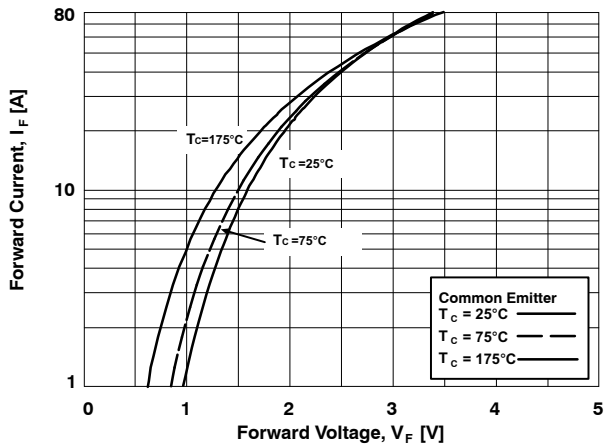


Figure 15. Forward Characteristics

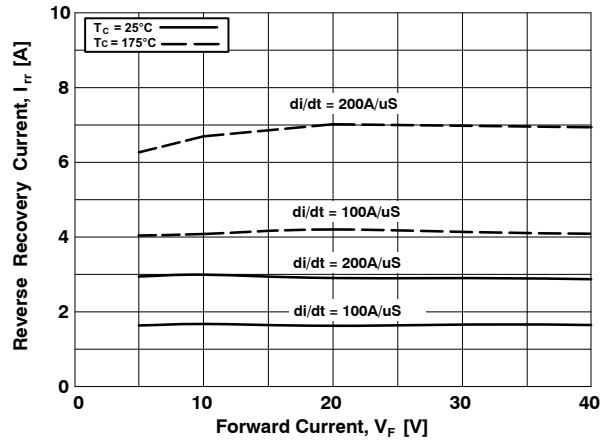


Figure 16. Reverse Recovery Current

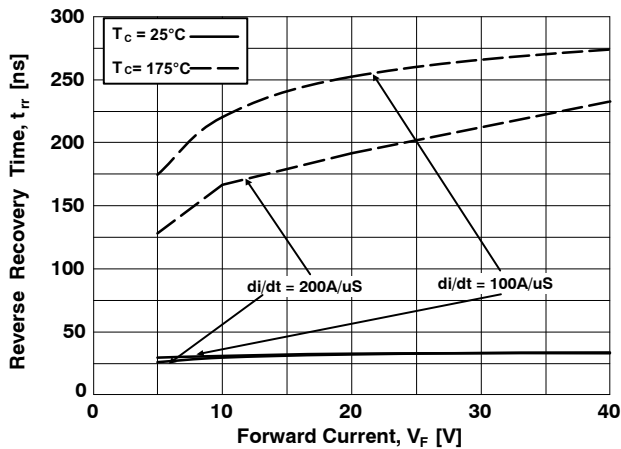


Figure 17. Reverse Recovery Time

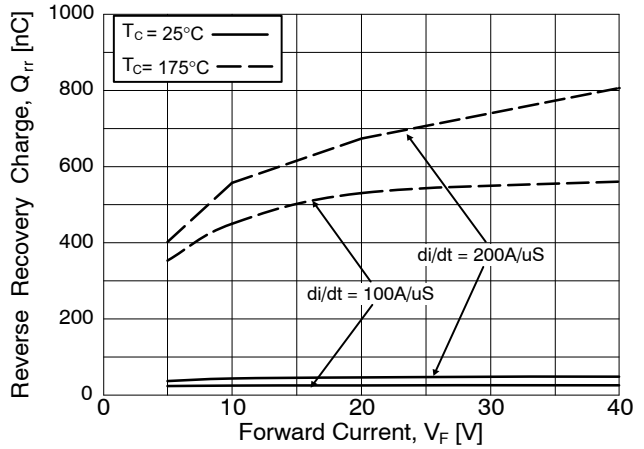


Figure 18. Stored Charge

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## TYPICAL CHARACTERISTICS (continued)

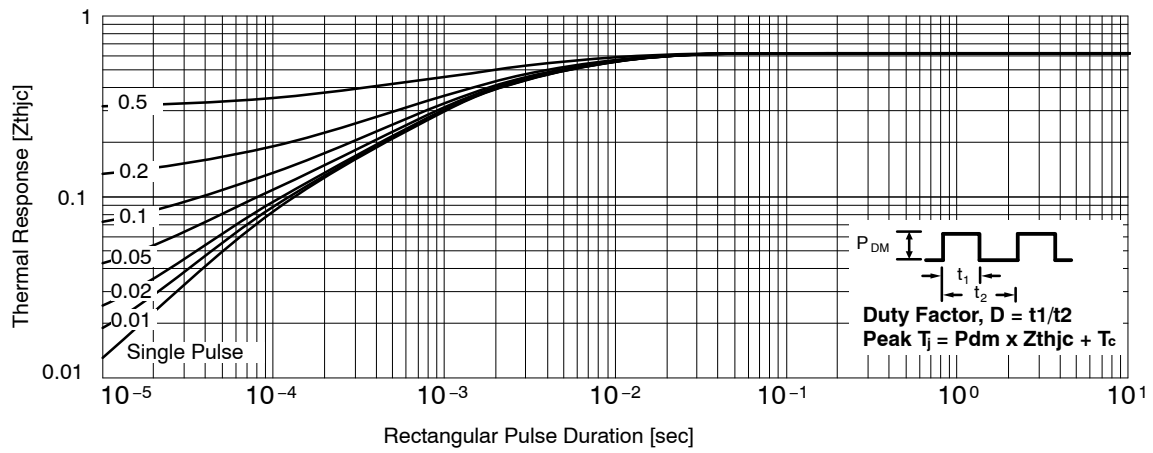


Figure 19. Transient Thermal Impedance of IGBT

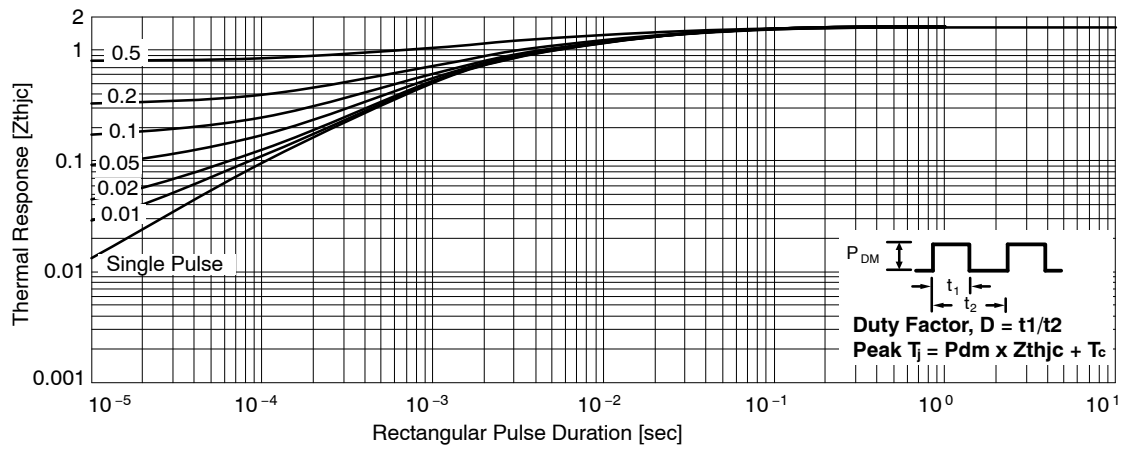


Figure 20. Transient Thermal Impedance of Diode

# MECHANICAL CASE OUTLINE

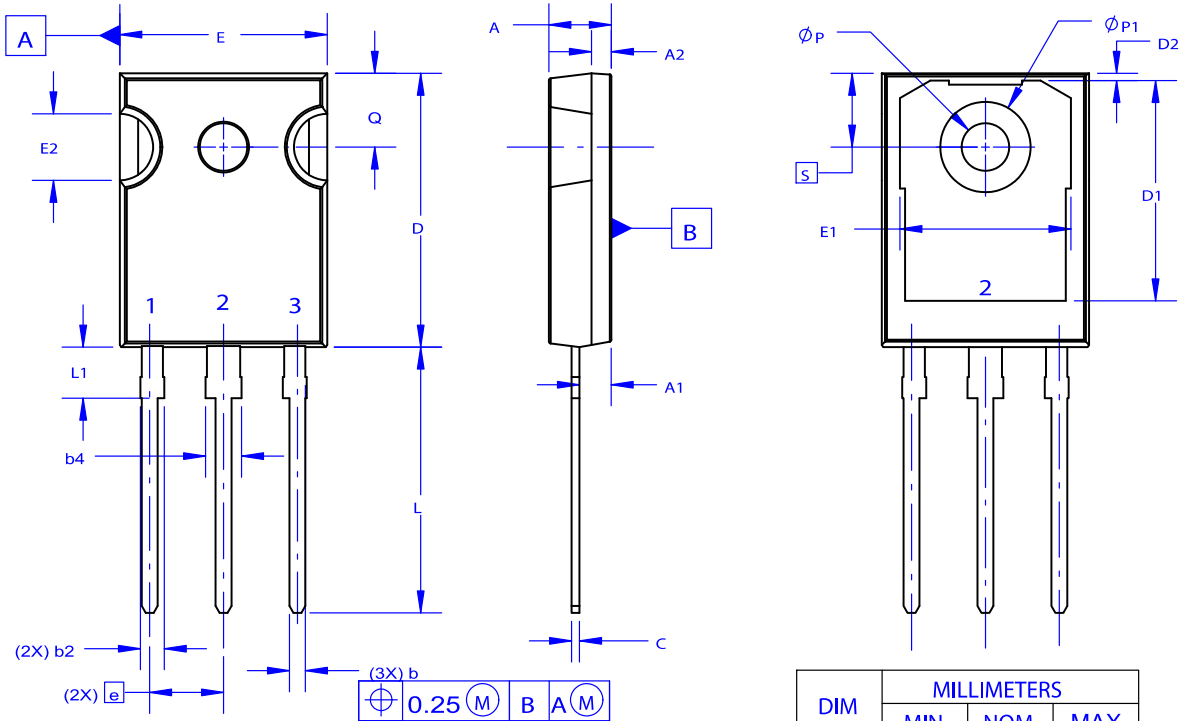
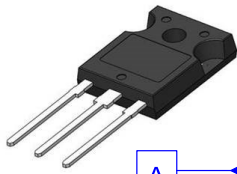
## PACKAGE DIMENSIONS

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TO-247-3LD  
CASE 340CX  
ISSUE A

DATE 06 JUL 2020



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

### GENERIC MARKING DIAGRAM\*



- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

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